AMENDMENTS TO THE SPECIFICATION

On page 26, please amend the paragraph beginning at line 20 and bridging to page 27, to read as follows:

[Example 1]

Fig. 1 shows a plan view and a sectional view illustrating one example of an electrode substrate and a thin film transistor of the present invention and their production methods. The lower electrode 2 and the insulating film 3 were layered sequentially in this order on the substrate 1, for example, with the same members and forming methods as in Fig. 13. However, in the present example, the pattern of a gate electrode to be the lower electrode 2 had two openings disposed adjacently to each other. In the present example, because the photosensitive lyophobic film 4 was coated by dip coating before backside exposure, the photosensitive lyophobic film 4 adhered to the surface of the insulating film 3 as well as to the back surface of the substrate 1 (Fig. 1(a)). With backside exposure, the photosensitive lyophobic film 4 was removed from the back surface of the substrate 1 to form a lyophobic region having a pattern approximately the same as that of the lower electrode 2 on the surface of the ~~insulating film 4~~ insulating film 3 (Figs. 1(b) and (c)). A conductive ink made of a liquid material containing at least one of a metal ultrafine particle material, a metal complex and a conductive polymer, was coated on two lyophilic regions surrounded by the lyophobic region, formed on the insulating film 3, and the coating ink was baked to form upper electrodes 5 and 6 (Fig. 1(d)). No particular constraint is imposed on the conductive ink, as long as the conductive ink is a liquid material having such properties that it is repelled from the lyophobic region formed of the photosensitive lyophobic film 4 and it wets and spreads over the lyophilic region from which the photosensitive lyophobic film 4 is removed, and exhibits a sufficiently low resistance value after baking; specific examples of such a material to be usable include a solution in which a metal ultrafine particle material of about 10 nm or less in

diameter or a metal complex, mainly composed of Au, Ag, Pd, Pt, Cu, Ni or the like, is dispersed in a solvent such as water, toluene or xylene. Further, for the purpose of forming ITO (indium tin oxide) as a transparent electrode material, a solution in which a metal alkoxide such as $In(O\text{-}i\text{-}C_3H_7)_3$ or $Sn(O\text{-}i\text{-}C_3H_7)_3$ is dispersed in a solvent such as water or an alcohol can be used. Furthermore, as the transparent electrode material other than this, an aqueous solution of PEDOT (poly-3,4-ethylenedioxythiophene), polyaniline (PAn), polypyrrole (PPy) or the like doped with PSS (polystyrene sulfonic acid) being a conductive polymer can also be used. It was possible to form the upper electrodes 5 and 6 each having a film thickness of about 100 nm with any one of the above described materials by dropping them in an amount enough to cover the above described two lyophilic regions and then baking them at an appropriate temperature of about 80 to 500°C under vacuum or in the air. In the present example, the upper electrodes 5 and 6 were formed as two rectangular shapes on the lyophilic regions other than the lyophobic region on the surface of the insulating film, and the pattern was a self-aligned shape in which the pattern of the lower electrode 2 was approximately inversed.